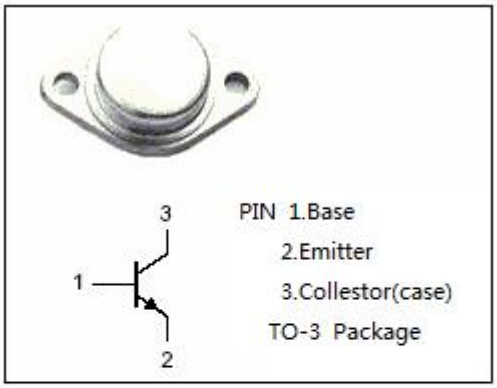
isc Silicon NPN Power Transistor 2N6217

DESCRIPTION

- With TO-3 package
- Excellent Safe Operating Area
- Low Collector-Emitter Saturation Voltage
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.



APPLICATIONS

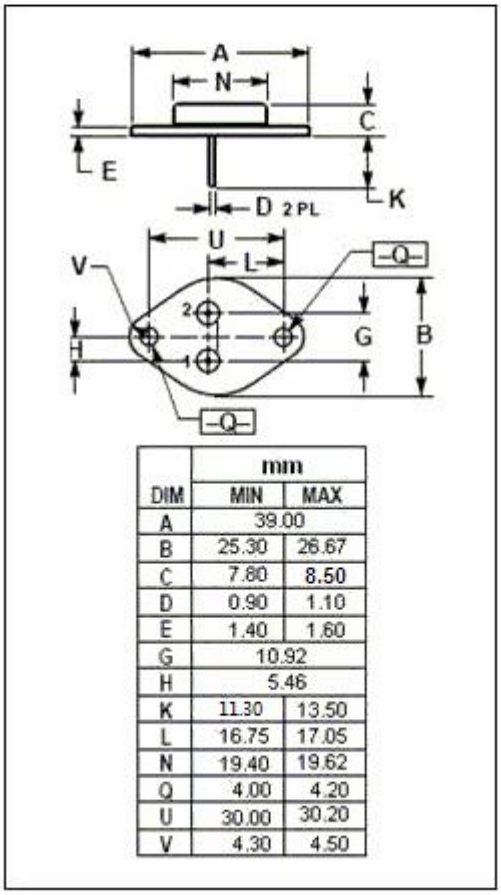
- Designed for linear power and switching amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	140	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
P_C	Collector Power Dissipation@T_C=100℃	71	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.46	℃/W



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C=30mA; I_B= 0	140			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 4A; I_B= 0.4A			1.2	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 6A; I_B= 0.75A			1.6	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C=6A; I_B= 0.75A			2.0	V
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 140V; I_B=0			0.5	mA
I_{CBO}	Collector Base Cutoff Current	V_{CB}=180V; I_E= 0			1.0	mA
h_{FE}	DC Current Gain	I_C= 5A; V_{CE}= 5V	20		80	
f_T	Current Gain-Bandwidth Product	I_C= 1A; V_{CE}= 10V; f= 1.0MHz		20		MHz